ESP32-MINI-1
ESP32-MINI-1U

Datasheet

2.4 GHz Wi-Fi + Bluetooth® + Bluetooth LE module

Built around ESP32 series of SoC, Xtensa® dual-core 32-bit LX6 microprocessor

4 MB flash

28 GPIOs, rich set of peripherals

On-board PCB antenna or external antenna connector

ESP32-MINI-1

ESP32-MINI-1U

Version 1.1

Espressif Systems

1 Module Overview

Note:

Check the link or the QR code to make sure that you use the latest version of this document:
https://espressif.com/sites/default/files/documentation/esp32-mini-1_datasheet_en.pdf

1.1 Features

CPU and On-Chip Memory

- ESP32-U4WDH embedded, Xtensa dual-core 32-bit LX6 microprocessor, up to 240 MHz
- 448 KB ROM
- 520 KB SRAM
- 16 KB SRAM in RTC
- 4 MB SPI flash

Wi-Fi

- 802.11b/g/n
- Bit rate: 802.11n up to 150 Mbps
- A-MPDU and A-MSDU aggregation
- 0.4 μs guard interval support
- Center frequency range of operating channel: 2412 ~ 2484 MHz

Bluetooth

- Bluetooth v4.2 BR/EDR and Bluetooth LE specification
- Class-1, class-2, and class-3 transmitter
- AFH
- CVSD and SBC

Peripherals

- SD card, UART, SPI, SDIO, I2C, LED PWM, motor PWM, I2S, infrared remote controller, pulse counter, GPIO, touch sensor, ADC, DAC, Ethernet, TWAI® (compatible with ISO 11898-1, i.e. CAN Specification 2.0)

Integrated Components on Module

- 40 MHz crystal oscillator

Antenna Options

- ESP32-MINI-1: On-board PCB antenna
- ESP32-MINI-1U: external antenna via a connector

Operating Conditions

- Operating voltage/Power supply: 3.0 ~ 3.6 V
- Operating ambient temperature:
  - 85 °C version module: –40 ~ 85 °C
  - 105 °C version module: –40 ~ 105 °C

Certification

- RF certification: CE/FCC/IC/SRRC
- Green certification: REACH/RoHS

Test

- Reliability: HTOL/HTSL/uHAST/TCT/ESD

1.2 Description

ESP32-MINI-1 and ESP32-MINI-1U are highly-integrated, small-sized Wi-Fi + Bluetooth + Bluetooth LE MCU modules that have a rich set of peripherals. The modules are ideal choices for a wide variety of IoT applications, ranging from home automation, smart building, consumer electronics to industrial control, especially suitable for applications within a compact space, such as bulbs, switches and sockets.

ESP32-MINI-1 comes with a on-board PCB antenna, and ESP32-MINI-1U with a connector for external antenna. Both ESP32-MINI-1 and ESP32-MINI-1U have two variants:

- 85 °C version: integrating the ESP32-U4WDH chip
- 105 °C version: integrating the ESP32-U4WDH chip

In this datasheet unless otherwise stated, ESP32-MINI-1 refers to both ESP32-MINI-1-N4 and ESP32-MINI-1-H4, whereas ESP32-MINI-1U refers to both ESP32-MINI-1U-N4 and ESP32-MINI-1U-H4.

The ordering information for ESP32-MINI-1 and ESP32-MINI-1U is listed as follows:

Table 1: Ordering Information

Module	Ordering code	Chip embedded	Module dimensions (mm)
ESP32-MINI-1 (85 °C version)	ESP32-MINI-1-N4	ESP32-U4WDH	13.2 × 19.0 × 2.4
ESP32-MINI-1 (105 °C version)	ESP32-MINI-1-H4	ESP32-U4WDH	
ESP32-MINI-1U (85 °C version)	ESP32-MINI-1U-N4	ESP32-U4WDH	13.2 × 13.5 × 2.4
ESP32-MINI-1U (105 °C version)	ESP32-MINI-1U-H4	ESP32-U4WDH	

At the core of this module is ESP32-U4WDH*, an Xtensa 32-bit LX6 CPU that operates at up to 240 MHz. The user can power off the CPU and make use of the low-power co-processor to constantly monitor the peripherals for changes or exceeding of thresholds.

This ESP32 chip integrates a rich set of peripherals, ranging from capacitive touch sensor, Hall sensor, SD card interface, Ethernet, high-speed SPI, UART, I2S, I2C, etc.

For more information on ESP32 chips, please refer to *ESP32 Series Datasheet*.

1.3 Applications

- Generic Low-power IoT Sensor Hub
- Generic Low-power IoT Data Loggers
- Cameras for Video Streaming
- Over-the-top (OTT) Devices
- Speech Recognition
- Image Recognition
- Mesh Network
- Home Automation
- Smart Building
- Industrial Automation
- Smart Agriculture
- Audio Applications
- Health Care Applications
- Wi-Fi-enabled Toys
- Wearable Electronics
- Retail & Catering Applications

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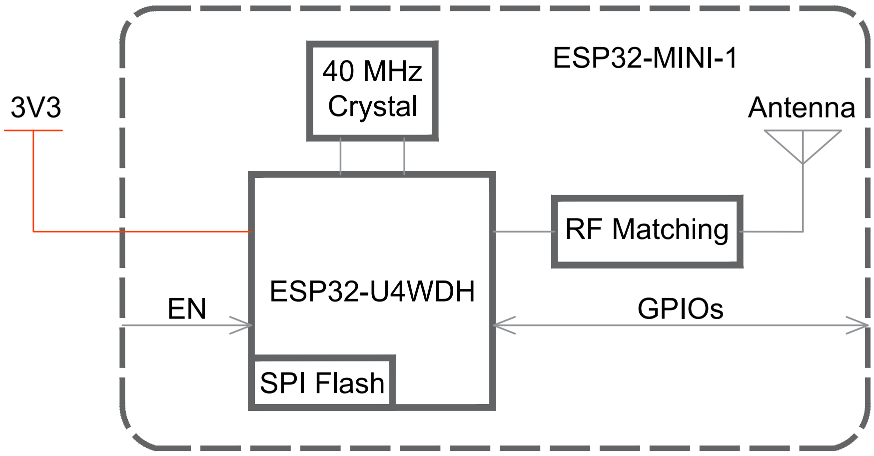

Figure 1: ESP32-MINI-1 Block Diagram

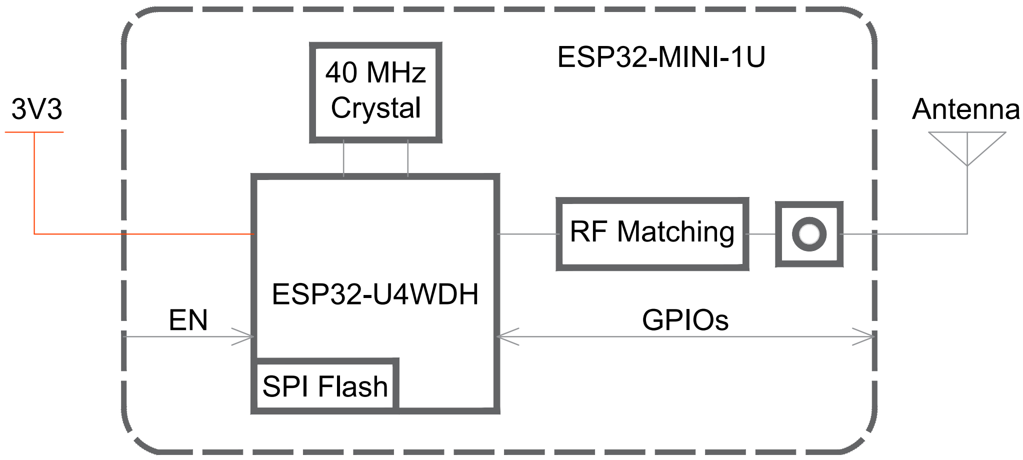

Figure 2: ESP32-MINI-1U Block Diagram

3 Pin Definitions

3.1 Pin Layout

The pin diagrams below show the approximate location of pins on the module. For the actual diagram drawn to scale, please refer to Figure 7.1 *Physical Dimensions*.

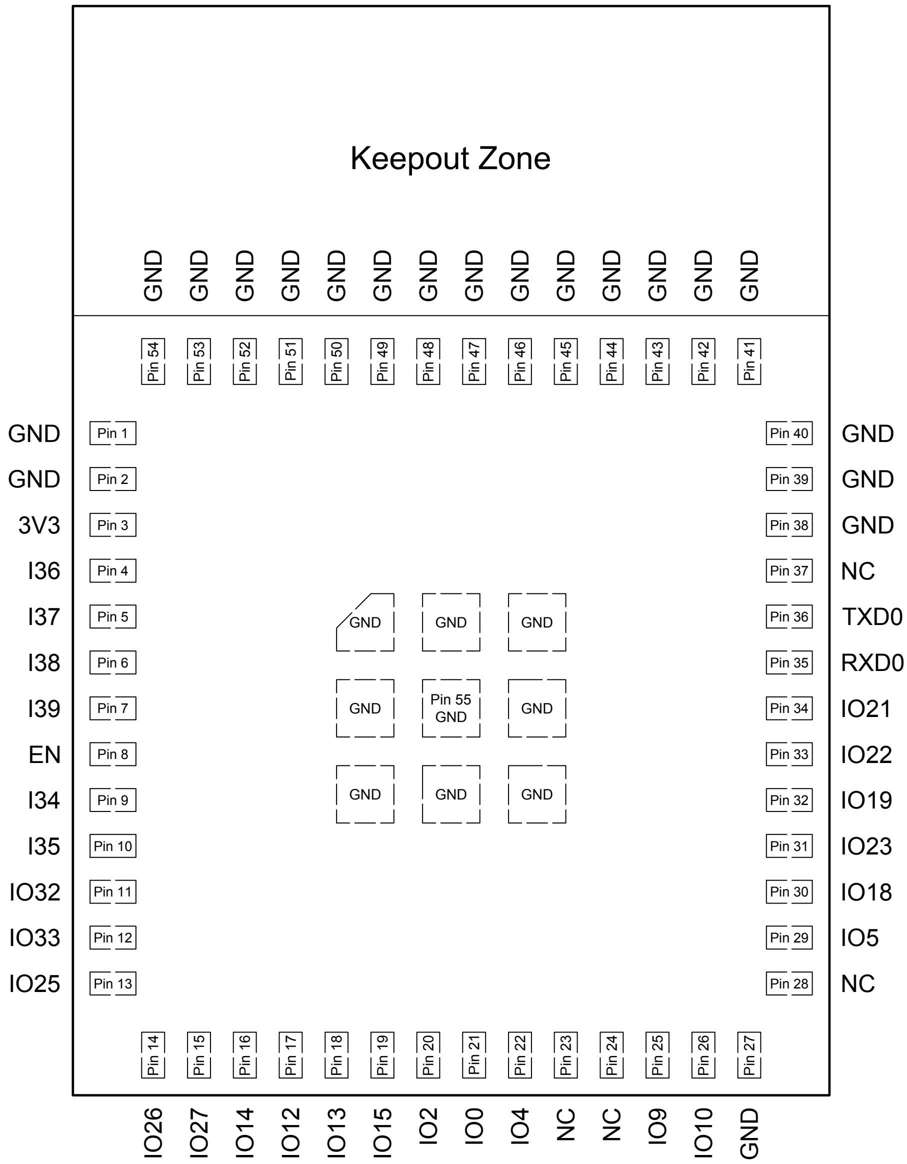

Figure 3: ESP32-MINI-1 Pin Layout (Top View)

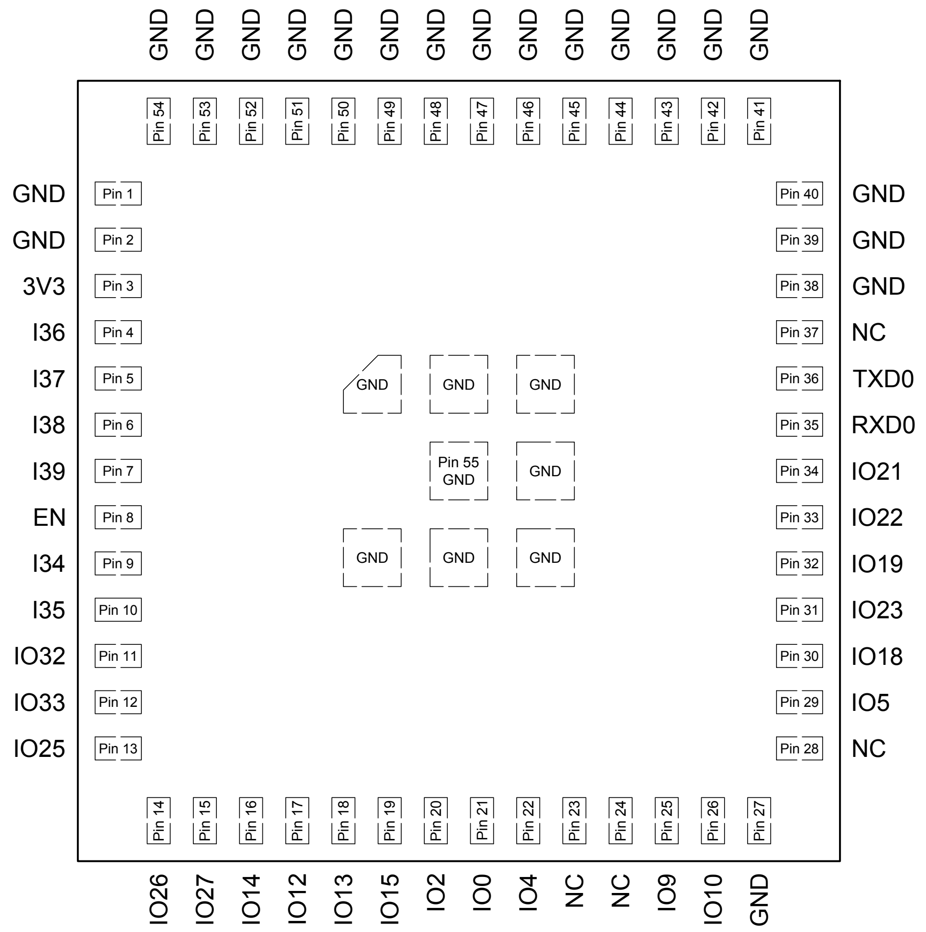

Figure 4: ESP32-MINI-1U Pin Layout (Top View)

3.2 Pin Description

ESP32-MINI-1 and ESP32-MINI-1U each has 55 pins. See pin definitions in Table 2. For peripheral pin configurations, please refer to *ESP32 Series Datasheet*.

Table 2: Pin Definitions

Name	No.	Type*	Function
GND	1, 2, 27, 38 ~ 55	P	Ground
3V3	3	P	Power supply
I36	4	I	GPIO36, ADC1_CH0, RTC_GPIO0
I37	5	I	GPIO37, ADC1_CH1, RTC_GPIO1
I38	6	I	GPIO38, ADC1_CH2, RTC_GPIO2
I39	7	I	GPIO39, ADC1_CH3, RTC_GPIO3
EN	8	I	High: enables the chip Low: the chip powers off Note: do not leave the pin floating
I34	9	I	GPIO34, ADC1_CH6, RTC_GPIO4
I35	10	I	GPIO35, ADC1_CH7, RTC_GPIO5

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Name	No.	Type	Function
IO32	11	I/O	GPIO32, XTAL_32K_P (32.768 kHz crystal oscillator input), ADC1_CH4, TOUCH9, RTC_GPIO9
IO33	12	I/O	GPIO33, XTAL_32K_N (32.768 kHz crystal oscillator output), ADC1_CH5, TOUCH8, RTC_GPIO8
IO25	13	I/O	GPIO25, DAC_1, ADC2_CH8, RTC_GPIO6, EMAC_RXD0
IO26	14	I/O	GPIO26, DAC_2, ADC2_CH9, RTC_GPIO7, EMAC_RXD1
IO27	15	I/O	GPIO27, ADC2_CH7, TOUCH7, RTC_GPIO17, EMAC_RX_DV
IO14	16	I/O	GPIO14, ADC2_CH6, TOUCH6, RTC_GPIO16, MTMS, HSPICLK, HS2_CLK, SD_CLK, EMAC_TXD2
IO12	17	I/O	GPIO12, ADC2_CH5, TOUCH5, RTC_GPIO15, MTDI, HSPIQ, HS2_DATA2, SD_DATA2, EMAC_TXD3
IO13	18	I/O	GPIO13, ADC2_CH4, TOUCH4, RTC_GPIO14, MTCK, HSPID, HS2_DATA3, SD_DATA3, EMAC_RX_ER
IO15	19	I/O	GPIO15, ADC2_CH3, TOUCH3, RTC_GPIO13, MTDO, HSPICS0, HS2_CMD, SD_CMD, EMAC_RXD3
IO2	20	I/O	GPIO2, ADC2_CH2, TOUCH2, RTC_GPIO12, HSPIWP, HS2_DATA0, SD_DATA0
IO0	21	I/O	GPIO0, ADC2_CH1, TOUCH1, RTC_GPIO11, CLK_OUT1, EMAC_TX_CLK
IO4	22	I/O	GPIO4, ADC2_CH0, TOUCH0, RTC_GPIO10, HSPIHD, HS2_DATA1, SD_DATA1, EMAC_TX_ER
NC	23	-	No connect
NC	24	-	No connect
IO9	25	I/O	GPIO9, HS1_DATA2, U1RXD, SD_DATA2
IO10	26	I/O	GPIO10, HS1_DATA3, U1TXD, SD_DATA3
NC	28	-	No connect
IO5	29	I/O	GPIO5, HS1_DATA6, VSPICS0, EMAC_RX_CLK
IO18	30	I/O	GPIO18, HS1_DATA7, VSPICLK
IO23	31	I/O	GPIO23, HS1_STROBE, VSPID
IO19	32	I/O	GPIO19, VSPIQ, U0CTS, EMAC_TXD0
IO22	33	I/O	GPIO22, VSPIWP, U0RTS, EMAC_TXD1
IO21	34	I/O	GPIO21, VSPIHD, EMAC_TX_EN
RXD0	35	I/O	GPIO3, U0RXD, CLK_OUT2
TXD0	36	I/O	GPIO1, U0TXD, CLK_OUT3, EMAC_RXD2
NC	37	-	No connect

* Pins GPIO6, GPIO7, GPIO8, GPIO11, GPIO16, and GPIO17 on the ESP32-U4WDH chip are connected to the SPI flash integrated on the module and are not led out.

* P: power supply; I: input; O: output.

3.3 Strapping Pins

Note:
The content below is excerpted from Section Strapping Pins in *ESP32 Series Datasheet*. For the strapping pin mapping between the chip and modules, please refer to Chapter 5 *Module Schematics*.

ESP32-U4WDH has five strapping pins:

- MTDI
- GPIO0
- GPIO2
- MTDO
- GPIO5

Software can read the values of these five bits from register "GPIO_STRAPPING".

During the chip's system reset release (power-on-reset, RTC watchdog reset and brownout reset), the latches of the strapping pins sample the voltage level as strapping bits of "0" or "1", and hold these bits until the chip is powered down or shut down. The strapping bits configure the device's boot mode, the operating voltage of VDD_SDIO and other initial system settings.

Each strapping pin is connected to its internal pull-up/pull-down during the chip reset. Consequently, if a strapping pin is unconnected or the connected external circuit is high-impedance, the internal weak pull-up/pull-down will determine the default input level of the strapping pins.

To change the strapping bit values, users can apply the external pull-down/pull-up resistances, or use the host MCU's GPIOs to control the voltage level of these pins when powering on ESP32-U4WDH.

After reset release, the strapping pins work as normal-function pins.

Refer to Table 3 for a detailed boot-mode configuration by strapping pins.

Table 3: Strapping Pins

Voltage of Internal LDO (VDD_SDIO)					
Pin	Default	3.3 V		1.8 V	
MTDI	Pull-down	0		1	
Booting Mode					
Pin	Default	SPI Boot		Download Boot	
GPIO0	Pull-up	1		0	
GPIO2	Pull-down	Don’t-care		0	
Enabling/Disabling Debugging Log Print over U0TXD During Booting					
Pin	Default	U0TXD Active		U0TXD Silent	
MTDO	Pull-up	1		0	
Timing of SDIO Slave					
Pin	Default	FE Sampling FE Output	FE Sampling RE Output	RE Sampling FE Output	RE Sampling RE Output
MTDO	Pull-up	0	0	1	1
GPIO5	Pull-up	0	1	0	1

* FE: falling-edge, RE: rising-edge
* Firmware can configure register bits to change the settings of ”Voltage of Internal LDO (VDD_SDIO)” and ”Timing of SDIO Slave”, after booting.
* The module integrates a 3.3 V SPI flash, so the pin MTDI cannot be set to 1 when the module is powered up.

4 Electrical Characteristics

4.1 Absolute Maximum Ratings

Stresses above those listed in *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Table 4: Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
VDD33	Power supply voltage	–0.3	3.6	V
T_{STORE}	Storage temperature	–40	105	°C

* Please see Appendix IO MUX of ESP32 Series Datasheet for IO's power domain.

4.2 Recommended Operating Conditions

Table 5: Recommended Operating Conditions

Symbol	Parameter		Min	Typ	Max	Unit
VDD33	Power supply voltage		3.0	3.3	3.6	V
I_{VDD}	Current delivered by external power supply		0.5	—	—	A
T	Operating ambient temperature	85 °C version	–40	—	85	°C
		105 °C version			105	

4.3 DC Characteristics (3.3 V, 25 °C)

Table 6: DC Characteristics (3.3 V, 25 °C)

Symbol	Parameter	Min	Typ	Max	Unit
C_{IN}	Pin capacitance	—	2	—	pF
V_{IH}	High-level input voltage	0.75 × VDD[1]	—	VDD[1]+ 0.3	V
V_{IL}	Low-level input voltage	–0.3	—	0.25 × VDD[1]	V
I_{IH}	High-level input current	—	—	50	nA
I_{IL}	Low-level input current	—	—	50	nA
V_{OH}	High-level output voltage	0.8 × VDD[1]	—	—	V
V_{OL}	Low-level output voltage	—	—	0.1 × VDD[1]	V

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Table 6 – cont'd from previous page

Symbol	Parameter		Min	Typ	Max	Unit
I_{OH}	High-level source current (VDD[1]= 3.3 V, V_{OH} >= 2.64 V, output drive strength set to the maximum)	VDD3P3_CPU power domain [1, 2]	—	40	—	mA
		VDD3P3_RTC power domain [1, 2]	—	40	—	mA
		VDD_SDIO power domain [1, 3]	—	20	—	mA
I_{OL}	Low-level sink current (VDD[1]= 3.3 V, V_{OL} = 0.495 V, output drive strength set to the maximum)		—	28	—	mA
R_{PU}	Resistance of internal pull-up resistor		—	45	—	kΩ
R_{PD}	Resistance of internal pull-down resistor		—	45	—	kΩ
V_{IL_nRST}	Low-level input voltage of CHIP_PU to power off the chip		—	—	0.6	V

[1] Please see Appendix IO MUX of *ESP32 Series Datasheet* for IO's power domain. VDD is the I/O voltage for a particular power domain of pins.

[2] For VDD3P3_CPU and VDD3P3_RTC power domain, per-pin current sourced in the same domain is gradually reduced from around 40 mA to around 29 mA, V_{OH}>=2.64 V, as the number of current-source pins increases.

[3] Pins occupied by flash and/or PSRAM in the VDD_SDIO power domain were excluded from the test.

4.4 Current Consumption Characteristics

Owing to the use of advanced power-management technologies, the module can switch between different power modes. For details on different power modes, please refer to Section *RTC and Low-Power Management* in *ESP32 Series Datasheet*.

Table 7: Current Consumption Depending on RF Modes

Work mode	Description		Peak (mA)
Active (RF working)	TX	802.11b, 20 MHz, 1 Mbps, @19.5 dBm	379
		802.11g, 20 MHz, 54 Mbps, @15 dBm	276
		802.11n, 20 MHz, MCS7, @13 dBm	258
		802.11n, 40 MHz, MCS7, @13 dBm	260
	RX[2]	802.11b/g/n, 20 MHz	112
		802.11n, 40 MHz	118

[1] The current consumption measurements are taken with a 3.3 V supply at 25 °C of ambient temperature at the RF port. All transmitters' measurements are based on a 100% duty cycle.

[2] The current consumption figures for in RX mode are for cases when the peripherals are disabled and the CPU idle.

Table 8: Current Consumption Depending on Work Modes

Work mode	Description		Current consumption (Typ)
Modem-sleep [1, 2]	The CPU is powered on [3]	240 MHz	30 ~ 68 mA
		160 MHz	27 ~ 44 mA
		Normal speed: 80 MHz	20 ~ 31 mA
Light-sleep	—		0.8 mA
Deep-sleep	The ULP coprocessor is powered on [4]		150 μA
	ULP sensor-monitored pattern [5]		100 μA @1% duty
	RTC timer + RTC memory		10 μA
	RTC timer only		5 μA
Power off	CHIP_PU is set to low level, the chip is powered off		1 μA

[1] The current consumption figures in Modem-sleep mode are for cases where the CPU is powered on and the cache idle.

[2] When Wi-Fi is enabled, the chip switches between Active and Modem-sleep modes. Therefore, current consumption changes accordingly.

[3] In Modem-sleep mode, the CPU frequency changes automatically. The frequency depends on the CPU load and the peripherals used.

[4] During Deep-sleep, when the ULP coprocessor is powered on, peripherals such as GPIO and RTC I2C are able to operate.

[5] The "ULP sensor-monitored pattern" refers to the mode where the ULP coprocessor or the sensor works periodically. When ADC works with a duty cycle of 1%, the typical current consumption is 100 μA.

4.5 Wi-Fi RF Characteristics

4.5.1 Wi-Fi RF Standards

Table 9: Wi-Fi RF Standards

Name		Description
Center frequency range of operating channel [1]		2412 ~ 2484 MHz
Wi-Fi wireless standard		IEEE 802.11b/g/n
Data rate	20 MHz	11b: 1, 2, 5.5 and 11 Mbps 11g: 6, 9, 12, 18, 24, 36, 48, 54 Mbps 11n: MCS0-7, 72.2 Mbps (Max)
	40 MHz	11n: MCS0-7, 150 Mbps (Max)
Antenna type		On-board PCB antenna, external antenna[2]

[1] Device should operate in the center frequency range allocated by regional regulatory authorities. Target center frequency range is configurable by software.

[2] For the modules that use external antennas, the output impedance is 50 Ω. For other modules without external antennas, the output impedance is irrelevant.

4.5.2 Transmitter Characteristics

Target TX power is configurable based on device or certification requirements. The default characteristics are provided in Table 10.

Table 10: TX Power Characteristics

Rate	Typ (dBm)
11b, 1 Mbps	19.5
11b, 11 Mbps	19.5
11g, 6 Mbps	18
11g, 54 Mbps	14
11n, HT20, MCS0	18
11n, HT20, MCS7	13
11n, HT40, MCS0	18
11n, HT40, MCS7	13

4.5.3 Receiver Characteristics

Table 11: RX Sensitivity Characteristics

Rate	Typ (dBm)
1 Mbps	–97
2 Mbps	–94
5.5 Mbps	–92
11 Mbps	–88
6 Mbps	–93
9 Mbps	–91
12 Mbps	–89
18 Mbps	–87
24 Mbps	–84
36 Mbps	–80
48 Mbps	–77
54 Mbps	–75
11n, HT20, MCS0	–92
11n, HT20, MCS1	–88
11n, HT20, MCS2	–86
11n, HT20, MCS3	–83
11n, HT20, MCS4	–80
11n, HT20, MCS5	–76
11n, HT20, MCS6	–74
11n, HT20, MCS7	–72
11n, HT40, MCS0	–89
11n, HT40, MCS1	–85
11n, HT40, MCS2	–83
11n, HT40, MCS3	–80
11n, HT40, MCS4	–76
11n, HT40, MCS5	–72
11n, HT40, MCS6	–71

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Table 11 – cont'd from previous page

Rate	Typ (dBm)
11n, HT40, MCS7	–69

Table 12: RX Maximum Input Level

Rate	Typ (dBm)
11b, 1 Mbps	5
11b, 11 Mbps	5
11g, 6 Mbps	0
11g, 54 Mbps	–8
11n, HT20, MCS0	0
11n, HT20, MCS7	–8
11n, HT40, MCS0	0
11n, HT40, MCS7	–8

Table 13: Adjacent Channel Rejection

Rate	Typ (dB)
11b, 11 Mbps	35
11g, 6 Mbps	27
11g, 54 Mbps	13
11n, HT20, MCS0	27
11n, HT20, MCS7	12
11n, HT40, MCS0	16
11n, HT40, MCS7	7

4.6 Bluetooth Radio

4.6.1 Receiver – Basic Data Rate

Table 14: Receiver Characteristics – Basic Data Rate

Parameter	Conditions	Min	Typ	Max	Unit
Sensitivity @0.1% BER	—	–90	–89	–88	dBm
Maximum received signal @0.1% BER	—	0	—	—	dBm
Co-channel C/I	—	—	+7	—	dB
Adjacent channel selectivity C/I	F = F0 + 1 MHz	—	—	–6	dB
	F = F0 – 1 MHz	—	—	–6	dB
	F = F0 + 2 MHz	—	—	–25	dB
	F = F0 – 2 MHz	—	—	–33	dB
	F = F0 + 3 MHz	—	—	–25	dB
	F = F0 – 3 MHz	—	—	–45	dB

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Table 14 – cont'd from previous page

Parameter	Conditions	Min	Typ	Max	Unit
Out-of-band blocking performance	30 MHz ~ 2000 MHz	–10	—	—	dBm
	2000 MHz ~ 2400 MHz	–27	—	—	dBm
	2500 MHz ~ 3000 MHz	–27	—	—	dBm
	3000 MHz ~ 12.5 GHz	–10	—	—	dBm
Intermodulation	—	–36	—	—	dBm

4.6.2 Transmitter – Basic Data Rate

Table 15: Transmitter Characteristics – Basic Data Rate

Parameter	Conditions	Min	Typ	Max	Unit
RF transmit power*	—	—	0	—	dBm
Gain control step	—	—	3	—	dB
RF power control range	—	–12	—	+9	dBm
+20 dB bandwidth	—	—	0.9	—	MHz
Adjacent channel transmit power	F = F0 ± 2 MHz	—	–55	—	dBm
	F = F0 ± 3 MHz	—	–55	—	dBm
	F = F0 ± > 3 MHz	—	–59	—	dBm
$\Delta\ f1_{\text{avg}}$	—	—	—	155	kHz
$\Delta\ f2_{\text{max}}$	—	127	—	—	kHz
$\Delta\ f2_{\text{avg}}/\Delta\ f1_{\text{avg}}$	—	—	0.92	—	—
ICFT	—	—	–7	—	kHz
Drift rate	—	—	0.7	—	kHz/50 μs
Drift (DH1)	—	—	6	—	kHz
Drift (DH5)	—	—	6	—	kHz

* There are a total of eight power levels from 0 to 7, and the transmit power ranges from –12 dBm to 9 dBm. When the power level rises by 1, the transmit power increases by 3 dB. Power level 4 is used by default and the corresponding transmit power is 0 dBm.

4.6.3 Receiver – Enhanced Data Rate

Table 16: Receiver Characteristics – Enhanced Data Rate

Parameter	Conditions	Min	Typ	Max	Unit
$\pi/4$ DQPSK					
Sensitivity @0.01% BER	—	–90	–89	–88	dBm
Maximum received signal @0.01% BER	—	—	0	—	dBm
Co-channel C/I	—	—	11	—	dB
Adjacent channel selectivity C/I	F = F0 + 1 MHz	—	–7	—	dB
	F = F0 – 1 MHz	—	–7	—	dB
	F = F0 + 2 MHz	—	–25	—	dB
	F = F0 – 2 MHz	—	–35	—	dB
	F = F0 + 3 MHz	—	–25	—	dB

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Table 16 – cont'd from previous page

Parameter	Conditions	Min	Typ	Max	Unit
	F = F0 – 3 MHz	—	–45	—	dB
8DPSK					
Sensitivity @0.01% BER	—	–84	–83	–82	dBm
Maximum received signal @0.01% BER	—	—	–5	—	dBm
C/I c-channel	—	—	18	—	dB
Adjacent channel selectivity C/I	F = F0 + 1 MHz	—	2	—	dB
	F = F0 – 1 MHz	—	2	—	dB
	F = F0 + 2 MHz	—	–25	—	dB
	F = F0 – 2 MHz	—	–25	—	dB
	F = F0 + 3 MHz	—	–25	—	dB
	F = F0 – 3 MHz	—	–38	—	dB

4.6.4 Transmitter – Enhanced Data Rate

Table 17: Transmitter Characteristics – Enhanced Data Rate

Parameter	Conditions	Min	Typ	Max	Unit
RF transmit power (see note under Table 15)	—	—	0	—	dBm
Gain control step	—	—	3	—	dB
RF power control range	—	–12	—	+9	dBm
$\pi/4$ DQPSK max w0	—	—	–0.72	—	kHz
$\pi/4$ DQPSK max wi	—	—	–6	—	kHz
$\pi/4$ DQPSK max |wi + w0|	—	—	–7.42	—	kHz
8DPSK max w0	—	—	0.7	—	kHz
8DPSK max wi	—	—	–9.6	—	kHz
8DPSK max |wi + w0|	—	—	–10	—	kHz
$\pi/4$ DQPSK modulation accuracy	RMS DEVM	—	4.28	—	%
	99% DEVM	—	100	—	%
	Peak DEVM	—	13.3	—	%
8 DPSK modulation accuracy	RMS DEVM	—	5.8	—	%
	99% DEVM	—	100	—	%
	Peak DEVM	—	14	—	%
In-band spurious emissions	F = F0 ± 1 MHz	—	–46	—	dBm
	F = F0 ± 2 MHz	—	–44	—	dBm
	F = F0 ± 3 MHz	—	–49	—	dBm
	F = F0 +/– > 3 MHz	—	—	–53	dBm
EDR differential phase coding	—	—	100	—	%

4.7 Bluetooth LE Radio

4.7.1 Receiver

Table 18: Receiver Characteristics – Bluetooth LE

Parameter	Conditions	Min	Typ	Max	Unit
Sensitivity @30.8% PER	—	–94	–93	–92	dBm
Maximum received signal @30.8% PER	—	0	—	—	dBm
Co-channel C/I	—	—	+10	—	dB
Adjacent channel selectivity C/I	F = F0 + 1 MHz	—	–5	—	dB
	F = F0 – 1 MHz	—	–5	—	dB
	F = F0 + 2 MHz	—	–25	—	dB
	F = F0 – 2 MHz	—	–35	—	dB
	F = F0 + 3 MHz	—	–25	—	dB
	F = F0 – 3 MHz	—	–45	—	dB
Out-of-band blocking performance	30 MHz ~ 2000 MHz	–10	—	—	dBm
	2000 MHz ~ 2400 MHz	–27	—	—	dBm
	2500 MHz ~ 3000 MHz	–27	—	—	dBm
	3000 MHz ~ 12.5 GHz	–10	—	—	dBm
Intermodulation	—	–36	—	—	dBm

4.7.2 Transmitter

Table 19: Transmitter Characteristics – Bluetooth LE

Parameter	Conditions	Min	Typ	Max	Unit
RF transmit power (see note under Table 15)	—	—	0	—	dBm
Gain control step	—	—	3	—	dB
RF power control range	—	–12	—	+9	dBm
Adjacent channel transmit power	F = F0 ± 2 MHz	—	–55	—	dBm
	F = F0 ± 3 MHz	—	–57	—	dBm
	F = F0 ± > 3 MHz	—	–59	—	dBm
$\Delta f1_{avg}$	—	—	—	265	kHz
$\Delta f2_{max}$	—	210	—	—	kHz
$\Delta f2_{avg}/\Delta f1_{avg}$	—	—	+0.92	—	—
ICFT	—	—	–10	—	kHz
Drift rate	—	—	0.7	—	kHz/50 μs
Drift	—	—	2	—	kHz

5 Module Schematics

This is the reference design of the module.

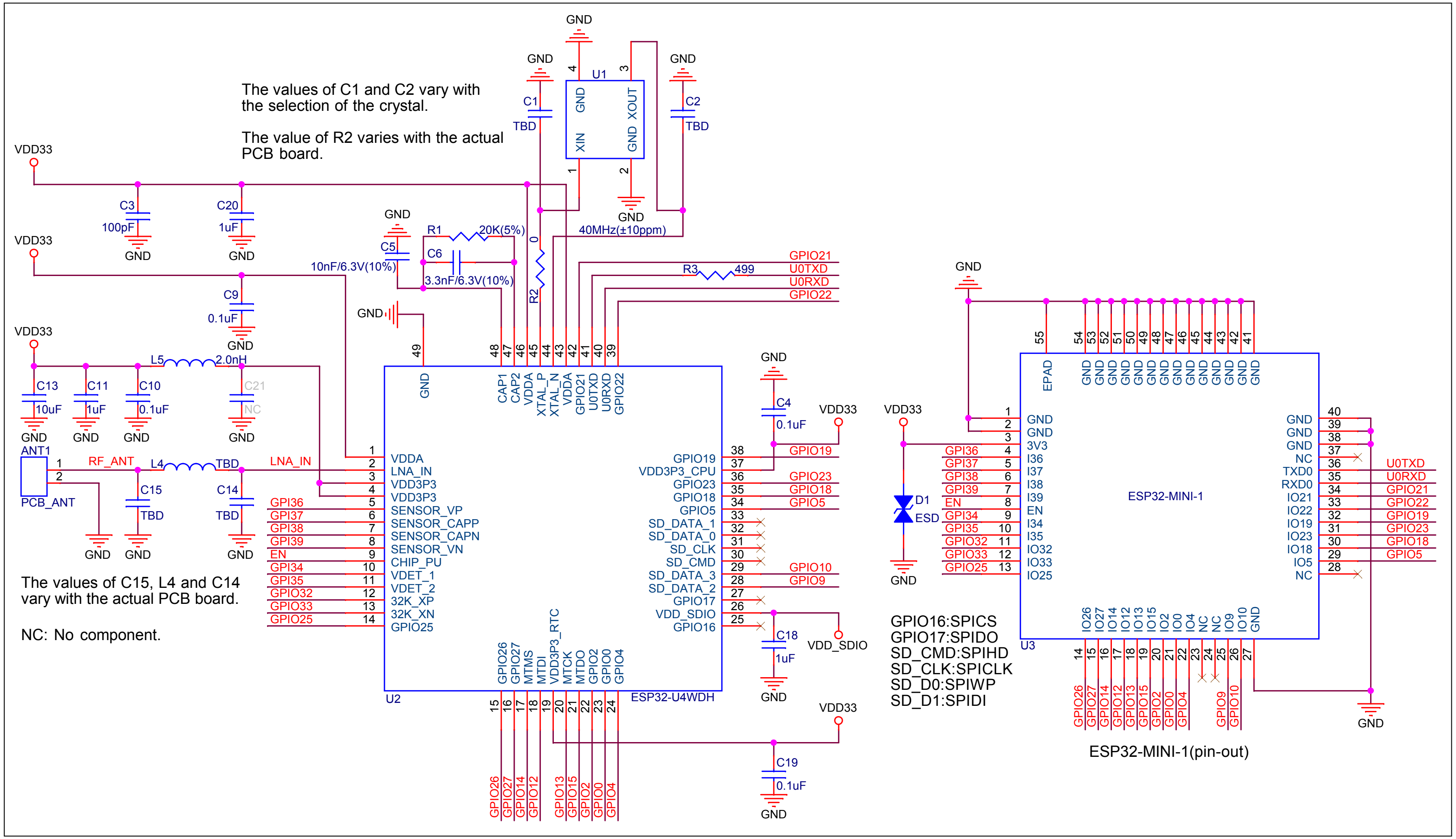


Figure 5: ESP32-MINI-1 Schematics

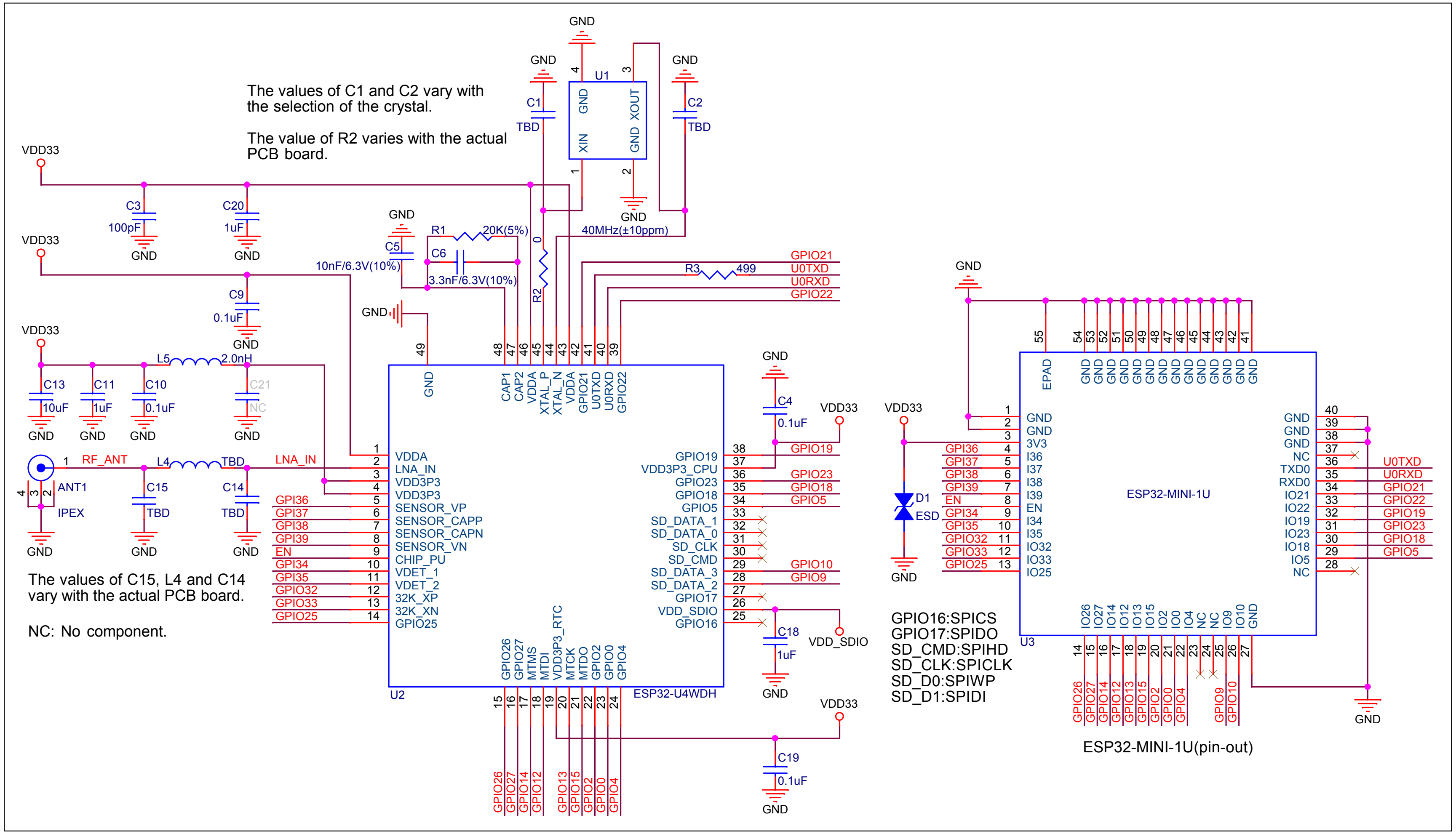


Figure 6: ESP32-MINI-1U Schematics

6 Peripheral Schematics

This is the typical application circuit of the module connected with peripheral components (for example, power supply, antenna, reset button, JTAG interface, and UART interface).

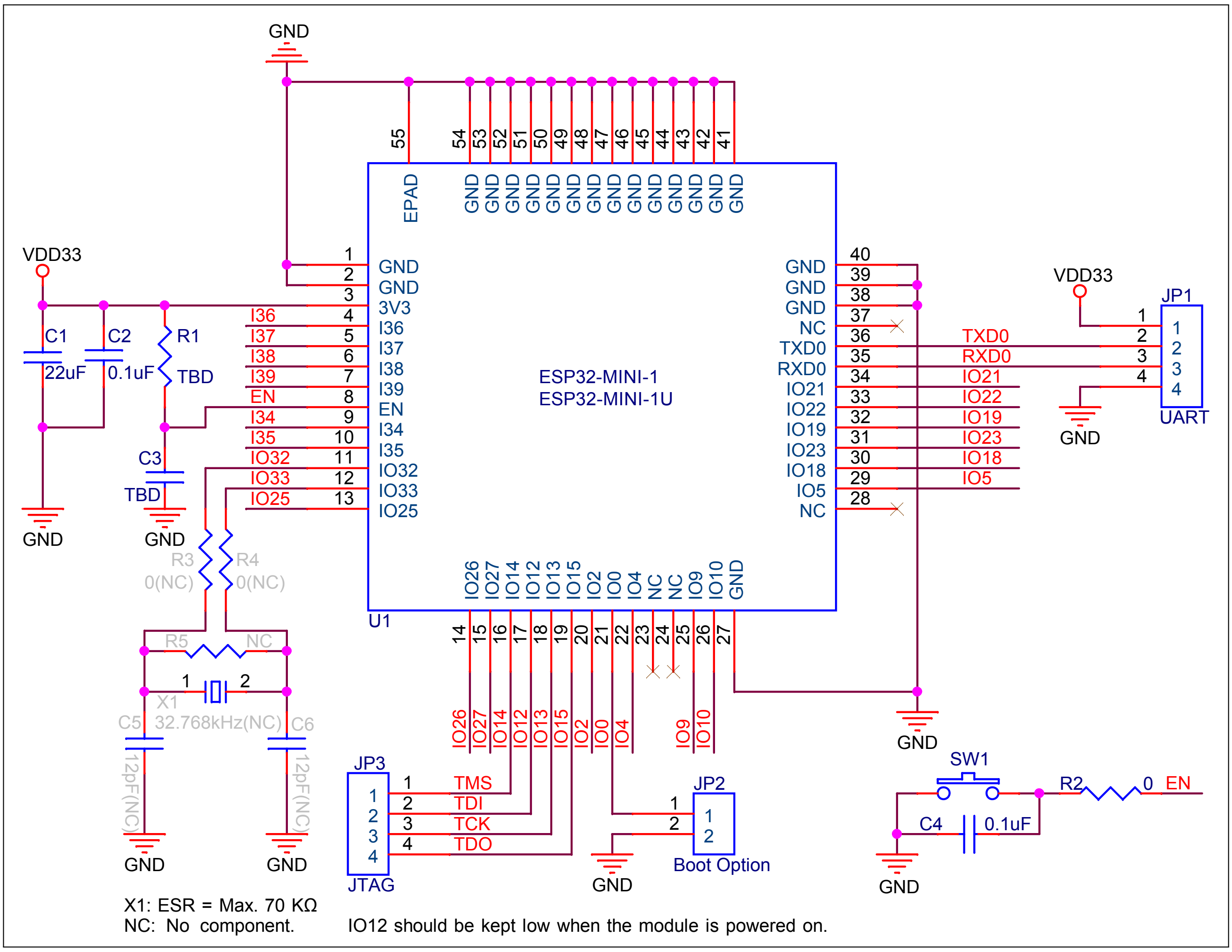


Figure 7: Peripheral Schematics

Note:

- Soldering Pad 55 to the Ground of the base board is not necessary for a satisfactory thermal performance. If users do want to solder it, they need to ensure that the correct quantity of soldering paste is applied.
- To ensure that the power supply to the ESP32 chip is stable during power-up, it is advised to add an RC delay circuit at the EN pin. The recommended setting for the RC delay circuit is usually R = 10 kΩ and C = 1 μF. However, specific parameters should be adjusted based on the power-up timing of the module and the power-up and reset sequence timing of the chip. For ESP32's power-up and reset sequence timing diagram, please refer to Section *Power Scheme* in ESP32 Series Datasheet.

7 Physical Dimensions and PCB Land Pattern

7.1 Physical Dimensions

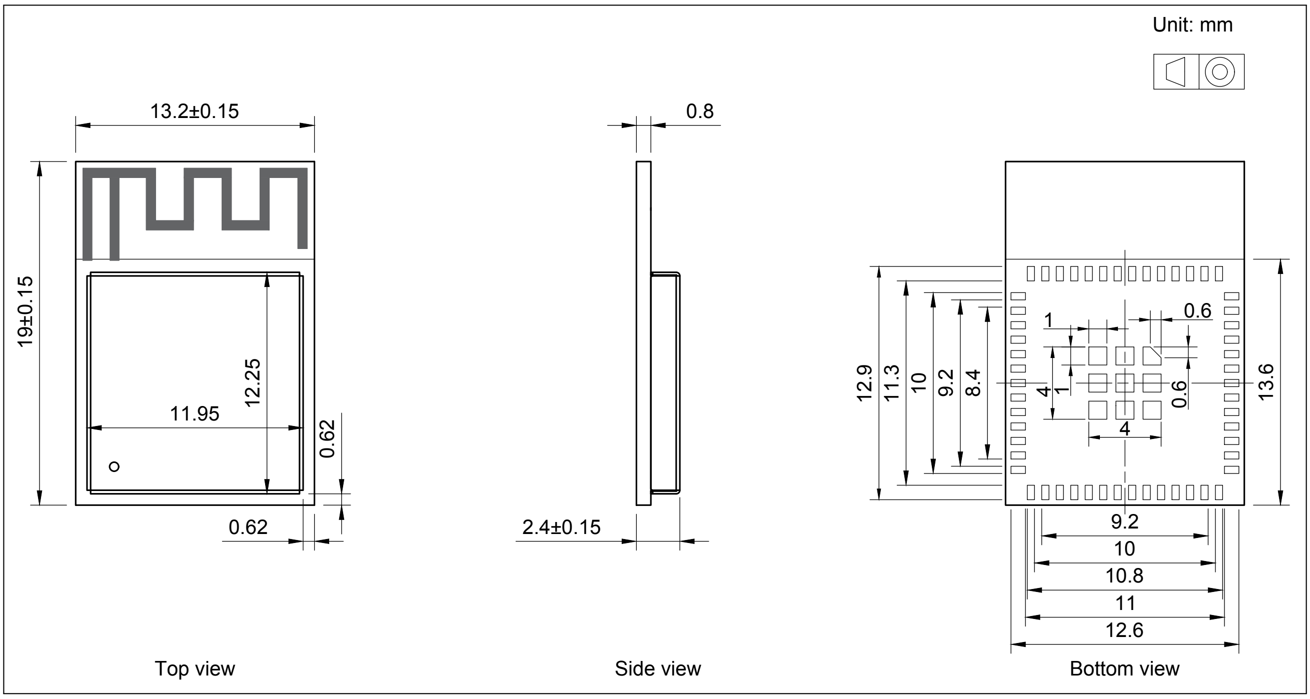


Figure 8: ESP32-MINI-1 Physical Dimensions

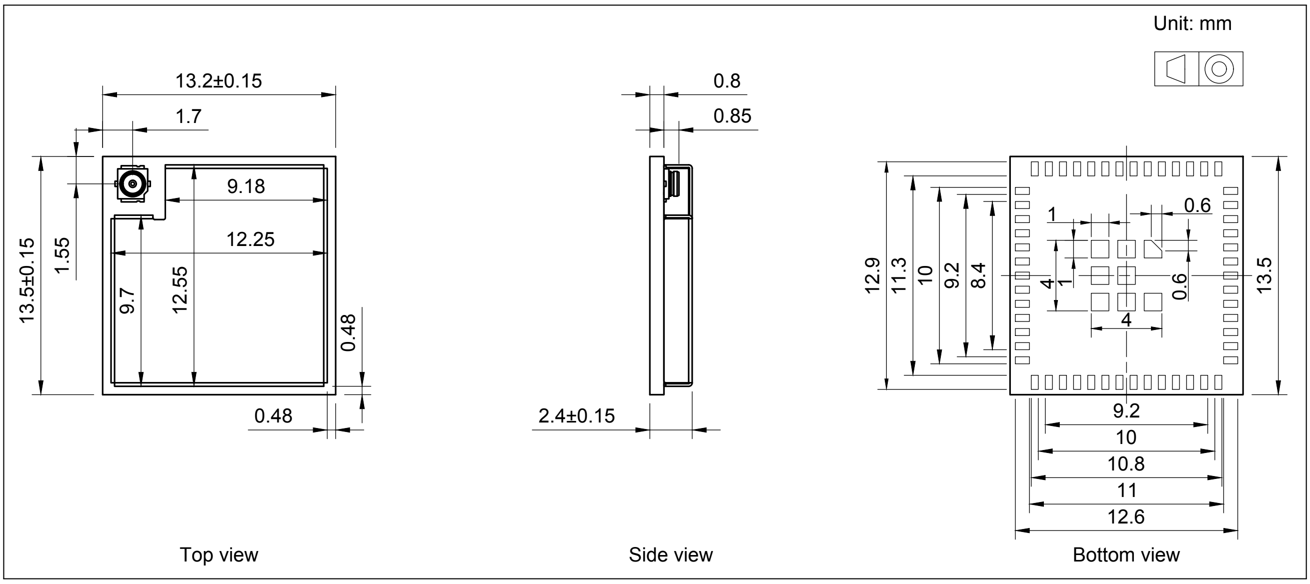


Figure 9: ESP32-MINI-1U Physical Dimensions

Note:

For information about tape, reel, and product marking, please refer to *Espressif Module Package Information*.

7.2 Recommended PCB Land Pattern

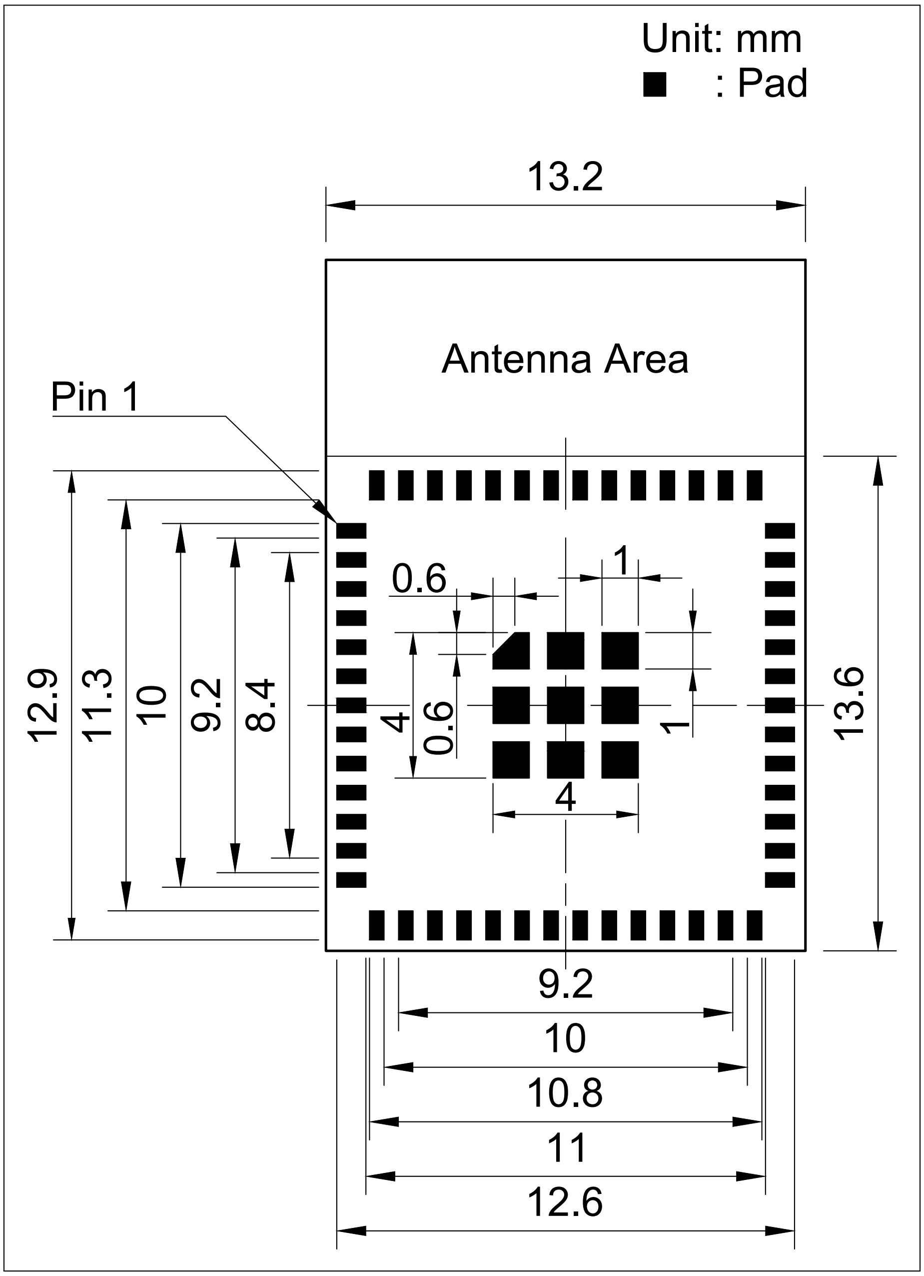


Figure 10: ESP32-MINI-1 Recommended PCB Land Pattern

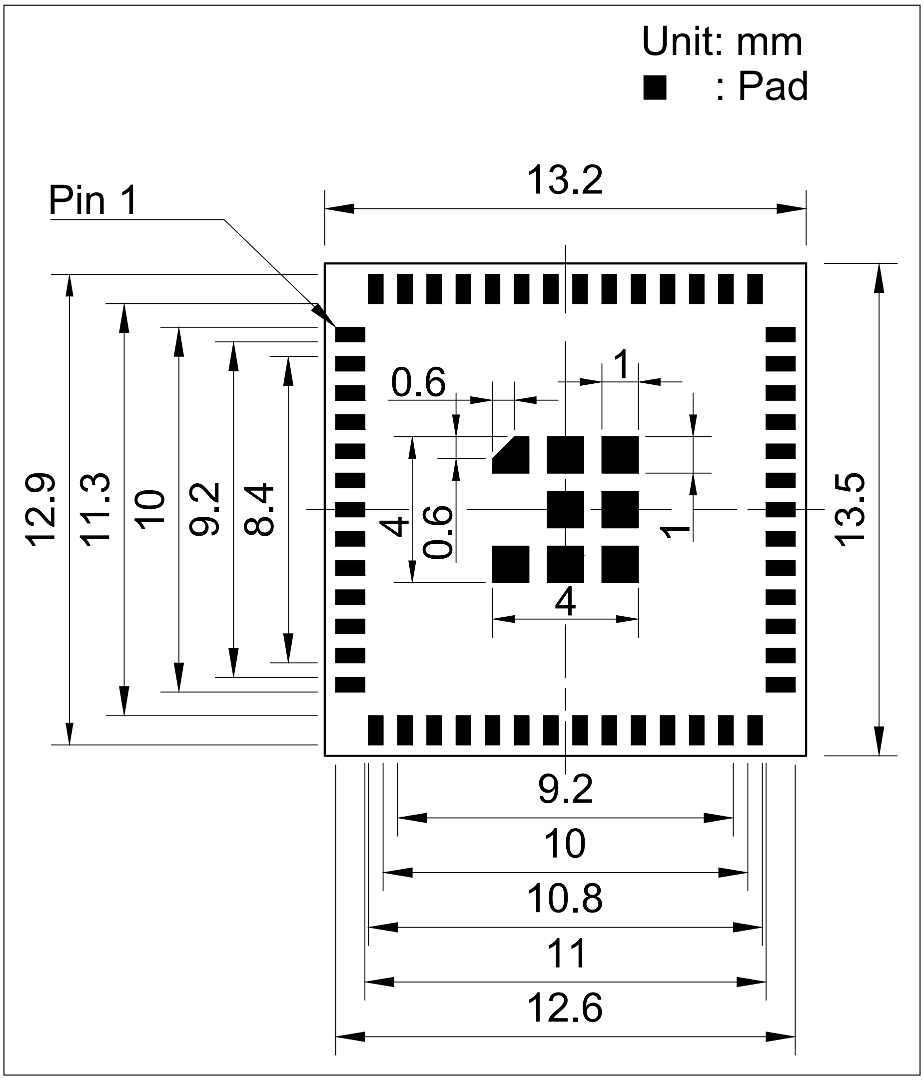


Figure 11: ESP32-MINI-1U PCB Recommended PCB Land Pattern

7.3 Dimensions of External Antenna Connector

ESP32-MINI-1U uses the third generation external antenna connector as shown in Figure 12. This connector is compatible with the following connectors:

- W.FL Series connector from Hirose
- MHF III connector from I-PEX
- AMMC connector from Amphenol

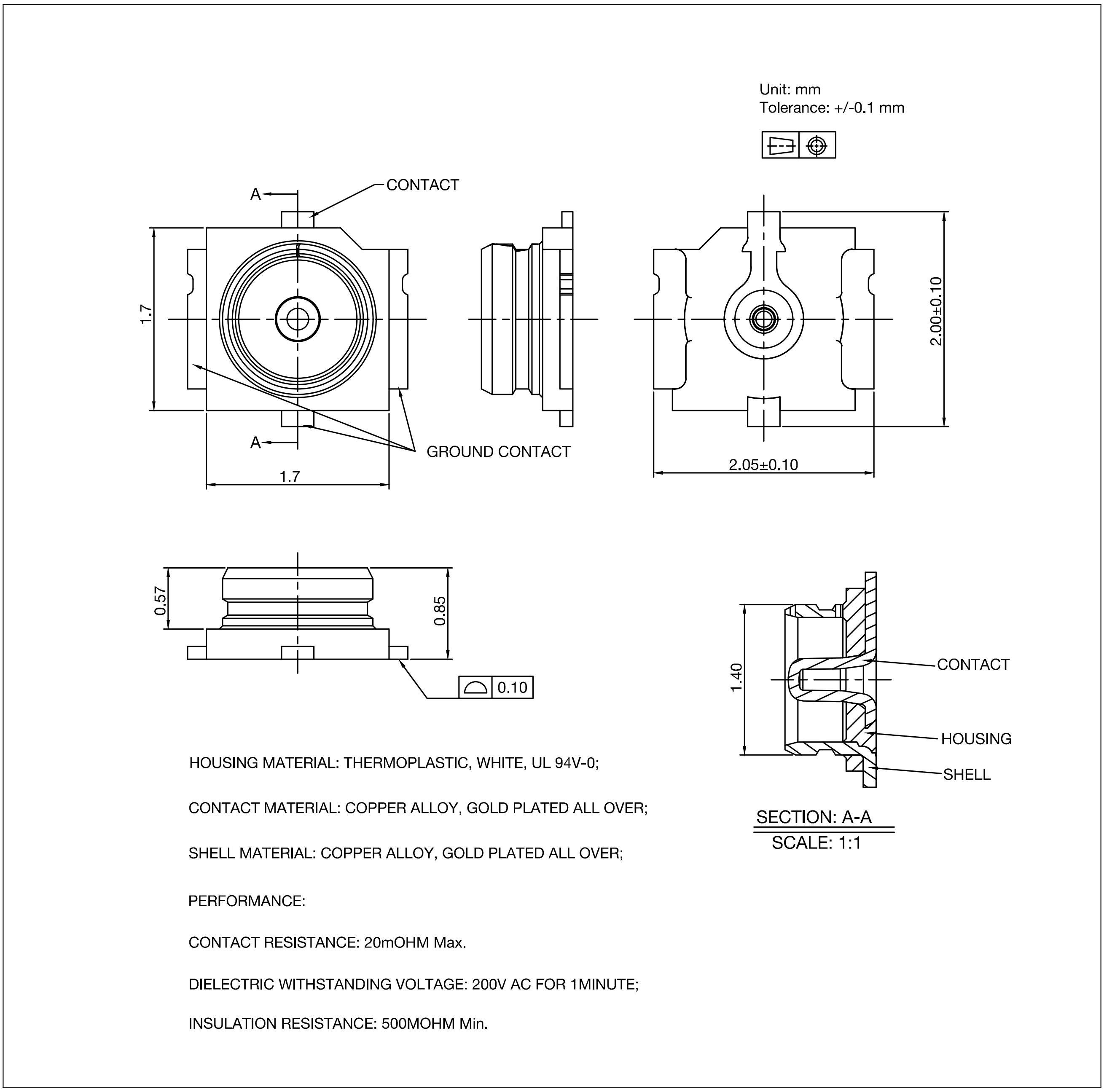


Figure 12: Dimensions of External Antenna Connector

8 Product Handling

8.1 Storage Conditions

The products sealed in moisture barrier bags (MBB) should be stored in a non-condensing atmospheric environment of < 40 °C and 90%RH. The module is rated at the moisture sensitivity level (MSL) of 3.

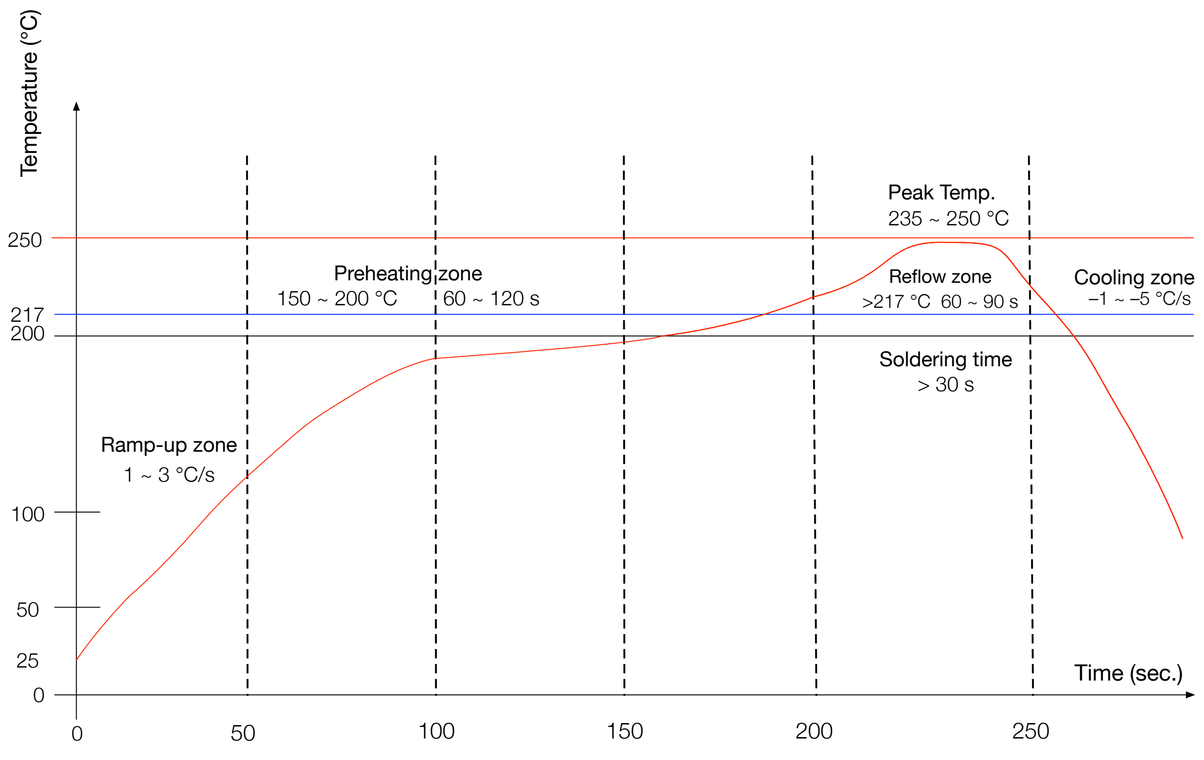
After unpacking, the module must be soldered within 168 hours with the factory conditions 25 ± 5 °C and 60 %RH. If the above conditions are not met, the module needs to be baked.

8.2 Electrostatic Discharge (ESD)

- Human body model (HBM): ±2000 V
- Charged-device model (CDM): ±500 V
- Air discharge: ±6000 V
- Contact discharge: ±4000 V

8.3 Reflow Profile

Solder the module in a single reflow.



Ramp-up zone — Temp.: 25 ~ 150 °C Time: 60 ~ 90 s Ramp-up rate: 1 ~ 3 °C/s
Preheating zone — Temp.: 150 ~ 200 °C Time: 60 ~ 120 s
Reflow zone — Temp.: >217 °C Time: 60 ~ 90 s; Peak Temp.: 235 ~ 250 °C Time: 30 ~ 70 s
Cooling zone — Peak Temp. ~ 180 °C Ramp-down rate: −1 ~ −5 °C/s
Solder — Sn-Ag-Cu (SAC305) lead-free solder alloy

Figure 13: Reflow Profile

9 Related Documentation and Resources

Related Documentation

- ESP32 Technical Reference Manual – Detailed information on how to use the ESP32 memory and peripherals.
- ESP32 Series Datasheet – Specifications of the ESP32 hardware.
- ESP32 Hardware Design Guidelines – Guidelines on how to integrate the ESP32 into your hardware product.
- ESP32 ECO and Workarounds for Bugs – Correction of ESP32 design errors.
- *Certificates*
  http://espressif.com/en/support/documents/certificates
- *ESP32 Product/Process Change Notifications (PCN)*
  http://espressif.com/en/support/documents/pcns
- *ESP32 Advisories* – Information on security, bugs, compatibility, component reliability.
  http://espressif.com/en/support/documents/advisories
- *Documentation Updates and Update Notification Subscription*
  http://espressif.com/en/support/download/documents

Developer Zone

- ESP-IDF Programming Guide for ESP32 – Extensive documentation for the ESP-IDF development framework.
- *ESP-IDF* and other development frameworks on GitHub.
  http://github.com/espressif
- *ESP32 BBS Forum* – Engineer-to-Engineer (E2E) Community for Espressif products where you can post questions, share knowledge, explore ideas, and help solve problems with fellow engineers.
  http://esp32.com/
- *The ESP Journal* – Best Practices, Articles, and Notes from Espressif folks.
  http://blog.espressif.com/
- See the tabs *SDKs and Demos*, *Apps*, *Tools*, *AT Firmware*.
  http://espressif.com/en/support/download/sdks-demos

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- *ESP32 Series SoCs* – Browse through all ESP32 SoCs.
  http://espressif.com/en/products/socs?id=ESP32
- *ESP32 Series Modules* – Browse through all ESP32-based modules.
  http://espressif.com/en/products/modules?id=ESP32
- *ESP32 Series DevKits* – Browse through all ESP32-based devkits.
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- *ESP Product Selector* – Find an Espressif hardware product suitable for your needs by comparing or applying filters.
  http://products.espressif.com/#/product-selector?language=en

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  http://espressif.com/en/contact-us/sales-questions

Revision History

Date	Version	Release notes
2021-11-09	v1.1	Upgraded the module embedded chip from single-core to dual-core [1] Updated the description to TWAI Updated Table 5: *Recommended Operating Conditions*
2021-07-14	v1.0	Added ESP32-MINI-1U module Updated the document formatting
2020-12-04	v0.5	Pre-release

[1]The module embedded chip (ESP32-U4WDH) is upgraded from single-core to dual-core, see PCN-2021-021. Estimated effective date: January 1, 2022. The single-core version coexists with the new dual-core version around January 1, 2022. The physical product is subject to batch tracking.